TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH4040FK

12-Stage Ripple-Carry Binary Counter

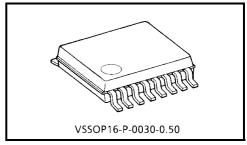
The TC7MH4040FK is an advanced high speed CMOS 12-stage ripple-carry binary counter fabricated with silicon gate $\rm C^2MOS$ technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

Setting CLR to high resets the counter to low.

A negative transition on the CK input brings one increment into the counter.

This counter provides all divided output stages, and at Q12, a 1/4096 divided frequency will be output.



Weight: 0.02 g (typ.)

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High speed: $f_{max} = 210 \text{ MHz}$ (typ.) (VCC = 5 V)
- Low power dissipation: $ICC = 4 \mu A \text{ (max) (Ta} = 25^{\circ}C)$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: tpLH = tpHL
- Wide operating voltage range: VCC (opr) = 2~5.5 V
- Low noise: VOLP = 1.5 V (max)
- Pin and function compatible with 74HC4040

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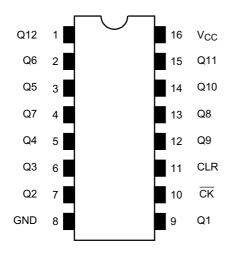
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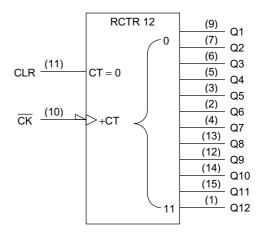
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Pin Assignment (top view)



IEC Logic Level



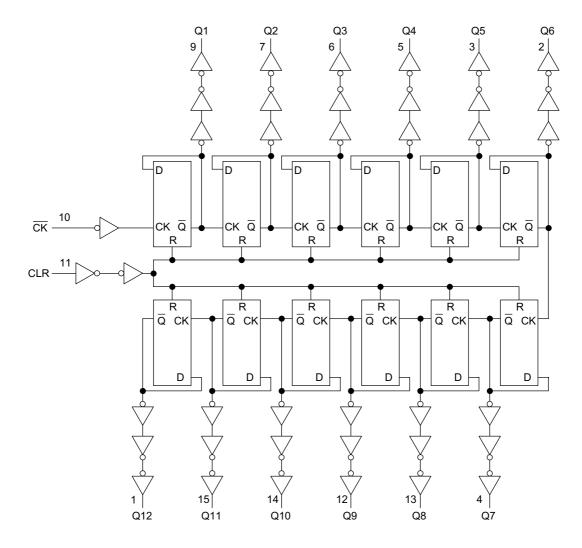
Truth Table

СК	CLR	Outputs
Х	Н	All outputs = "L"
	L	No change
	L	Advance to next statge

X: Don't care



System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±100	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C



Recommended Operating Conditions

Characteristics	Symbol Rating		Unit
Supply voltage	ly voltage V _{CC}		V
Input voltage	V _{IN} 0~5.5		V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100 \ (V_{CC} = 3.3 \pm 0.3 \ V)$ $0\sim20 \ (V_{CC} = 5 \pm 0.5 \ V)$	ns/V

Electrical Characteristics

DC Characteristics

Characteristics Symbo		Symbol	Test Condition		Ta = 25°C			Ta = -40~85°C		Unit	
Cilarac	Symbol Test Condition		V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit		
					2.0	1.50	_	_	1.50	_	
Input voltage	High level	V _{IH}	_		3.0~5.5	V _{CC} ×0.7		_	V _{CC} ×0.7		V
input voitage					2.0	_	_	0.50	_	0.50	V
	Low level	V _{IL}	_		3.0~5.5	_	_	V _{CC} × 0.3	_	$\begin{array}{c} V_{CC} \\ \times 0.3 \end{array}$	
		Vон	V _{IN} = V _{IH} or V _{IL}	Ι _{ΟΗ} = –50 μΑ	2.0	1.9	2.0	_	1.9	_	V
	High level				3.0	2.9	3.0	_	2.9	_	
					4.5	4.4	4.5		4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
Output				$I_{OH} = -8 \text{ mA}$	4.5	3.94		—	3.80		
voltage		V _{OL}			2.0	_	0	0.1	_	0.1	V
				$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1	
	Low level		$V_{IN} = V_{IH}$ or V_{IL}		4.5	_	0	0.1	_	0.1	
			0. 412	I _{OL} = 4 mA	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44	
Input leakage	current	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μΑ
Quiescent sup	ply current	I _{CC}	V _{IN} = V _{CC} or GND		5.5	_	_	4.0		40.0	μΑ

Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = -40~85°C	Unit
Characteristics Symbol		rest Condition	V _{CC} (V)	Typ. Limit		Limit	Offic
Minimum pulse width	t _{w (L)}		3.3 ± 0.3		5.0	5.0	ns
(CK)	t _{w (H)}	_	5.0 ± 0.5	_	5.0	5.0	
Minimum pulse width	4		3.3 ± 0.3		5.0	5.0	
(CLR)	t _{w (H)}	_	5.0 ± 0.5		5.0	5.0	ns
Minimum removal time		_	3.3 ± 0.3		5.0	5.0	20
	t _{rem}		5.0 ± 0.5	_	5.0	5.0	ns



AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol Test Condition	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Onaraciensiles C		rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
			3.3 ± 0.3	15		7.5	11.9	1.0	14.0	ns
Propagation delay time	t _{pLH}		3.3 ± 0.3	50		10.0	15.4	1.0	17.5	
(CK - Q1)	tpHL	_	5.0 ± 0.5	15		4.8	7.3	1.0	8.5	113
			3.0 ± 0.5	50		6.3	9.3	1.0	10.5	
Propagation delay time	A+ .		3.3 ± 0.3	50	_	2.4	4.4	1.0	5.0	ns
$(Q_n - Q_n + 1)$	Δt_{pd}		5.0 ± 0.5	50	_	1.6	3.1	1.0	3.5	115
	t _{pHL}	_	3.3 ± 0.3	15		8.3	12.8	1.0	15.0	- ns
Propagation delay time				50	_	10.8	16.3	1.0	18.5	
(CLR - Q)			5.0 ± 0.5	15		5.6	8.6	1.0	10.0	
				50		7.1	10.6	1.0	12.0	
			3.3 ± 0.3	15	75	140		75		- MHz
Maximum clock frequency				50	55	80		50		
Maximum clock frequency	f _{max}	_	5.0 ± 0.5	15	150	210		125		
			3.0 ± 0.3	50	95	125	_	80	_	
Input capacitance	C _{IN}	_	_		_	4	10	_	10	pF
Power dissipation capacitance	C _{PD}			(Note)	_	21	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

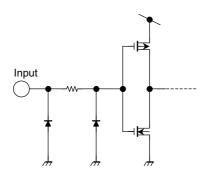
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

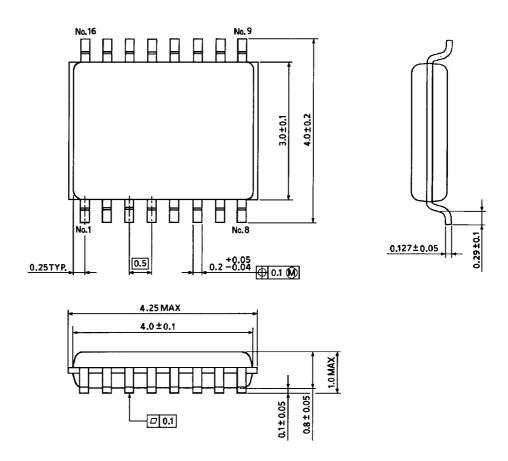
Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Characteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	1.2	1.5	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-1.2	-1.5	V
Minimum high level dynamic input voltage $V_{\mbox{\scriptsize IH}}$	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Minimum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0		1.5	V

Input Equivalent Circuit



Package Dimensions



Weight: 0.02 g (typ.)